



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

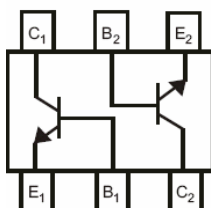
SOT-563 Plastic-Encapsulate Transistors

BC847BV DUAL TRANSISTOR(NPN)

SOT-563

FEATURES

- Epitaxial Die Construction
- Complementary PNP Type Available (BC857BV)
- Ultra-Small Surface Mount Package



Marking: K4V

MAXIMUM RATINGS($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Power Dissipation	0.15	W
$R_{\theta JA}$	Thermal Resistance. Junction to Ambient Air	833	$^{\circ}\text{C/W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			15	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			100	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=2\text{mA}$	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$ $I_C=100\text{mA}, I_B=5\text{mA}$			100 300	mV
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$ $I_C=100\text{mA}, I_B=5\text{mA}$		700 900		mV
Base-emitter voltage	V_{BE}	$V_{CE}=5\text{V}, I_C=2\text{mA}$ $V_{CE}=5\text{V}, I_C=10\text{mA}$	580	660	700 770	mV
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100			MHz
Output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			4.5	pF
Noise Figure	NF	$V_{CE}=5\text{V}, R_s=2\text{k}\Omega,$ $f=1\text{kHz}, BW=200\text{Hz}$			10	dB

Typical Characteristics

BC847BV

